

N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56 20 October 2016

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

Features and benefits 2.

- Advanced TrenchMOS provides low R_{DSon} and low gate charge •
- Logic level gate operation
- Avalanche rated, 100% tested •
- LFPAK provides maximum power density in a Power SO8 package

Applications 3.

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- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications •
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

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1.1.1

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | - | 80 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | - | 100 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 238 | W |
| Static chara | acteristics | | | | _ | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u> | | - | 6.3 | 8.5 | mΩ |
| Dynamic cl | naracteristics | | | 1 | | | |
| Q _{GD} | gate-drain charge | $I_{D} = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$ | | - | 17.1 | - | nC |

[1] Continuous current is limited by package.

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5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S | source | mb | D |
| 2 | S | source | | |
| 3 | S | source | q | G-UTA |
| 4 | G | gate | មុច្ចថ្ | mbb076 S |
| mb | D | mounting base; connected to drain | 1 2 3 4 LFPAK56; Power- SO8 (SOT669) | |

6. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|-----------------------|--|---------|--|--|--|
| Type number | Package | age | | | | |
| | Name | Description | Version | | | |
| PSMN8R0-80YL | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 | | | |

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | 80 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | | - | 80 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | 238 | W |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | 100 | Α |
| | | V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u> | [1] | - | 75 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | | - | 423 | А |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-dra | in diode | | | 1 | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 100 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 423 | А |

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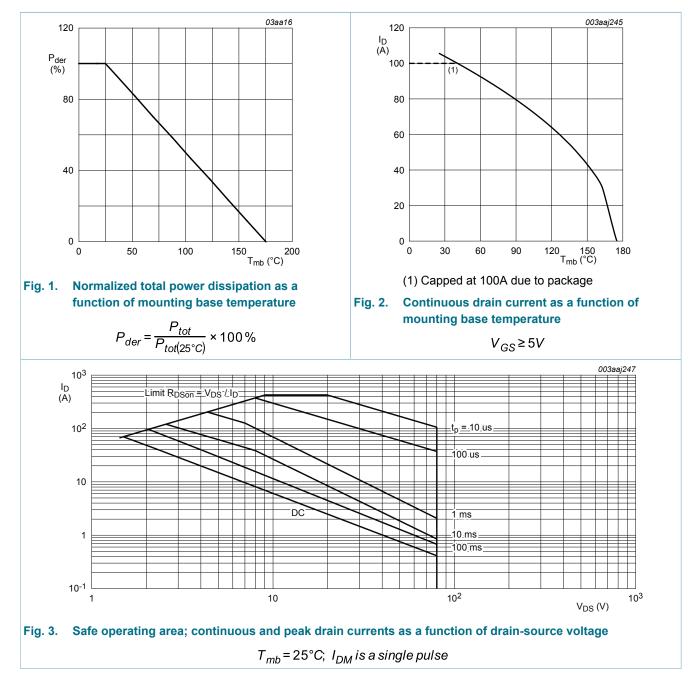
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| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|----------------------|---|---|----------------|-----|-----|------|
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\begin{split} I_D &= 100 \text{ A}; \text{ V}_{sup} \leq 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; \\ \text{V}_{GS} &= 5 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$ | [<u>2][3]</u> | - | 148 | mJ |

[1]

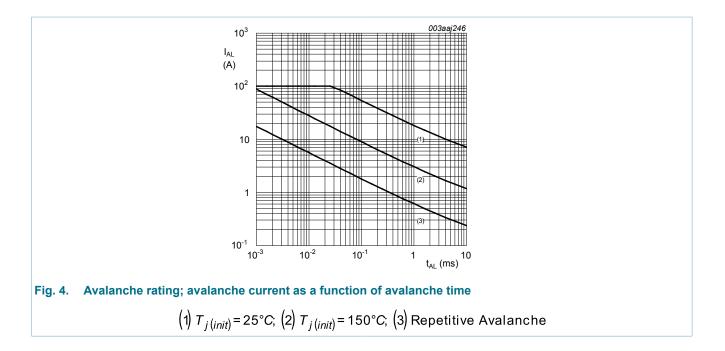
Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.



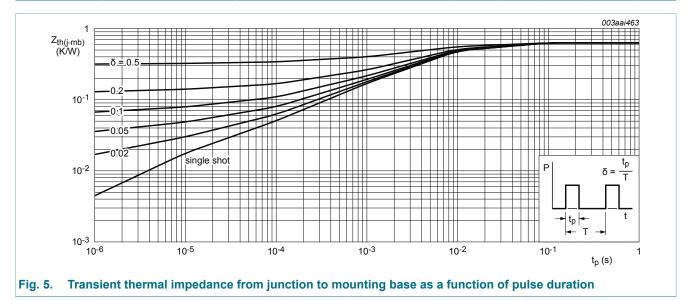
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8. Thermal characteristics

| Table 5. Thermal characteristics | | | | | | | |
|----------------------------------|---|------------|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | | - | - | 0.63 | K/W |



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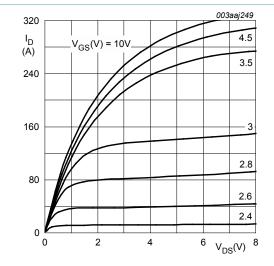
9. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|-------------------------------|--|-----|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 80 | - | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C | 72 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u> | 1.4 | 1.7 | 2.1 | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u> | - | - | 2.45 | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u> | 0.5 | - | - | V |
| I _{DSS} | drain leakage current | V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| | | V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.07 | 10 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} drain-source resistance | drain-source on-state | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u> | - | 6.3 | 8.5 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 5.8 | 8 | mΩ |
| | | V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | - | 21.3 | mΩ |
| Dynamic cl | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; \text{ V}_{DS} = 64 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$ | - | 104 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ | - | 54.7 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13; Fig. 14</u> | - | 13.5 | - | nC |
| Q _{GD} | gate-drain charge | | - | 17.1 | - | nC |
| C _{iss} | input capacitance | V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; | - | 6125 | 8167 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | - | 397 | 476 | pF |
| C _{rss} | reverse transfer capacitance | | - | 207 | 284 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 5 V; | - | 28 | - | ns |
| t _r | rise time | R _{G(ext)} = 5 Ω; T _j = 25 °C | - | 50 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 82 | - | ns |
| t _f | fall time | | - | 45 | - | ns |
| Source-dra | in diode | | I | 1 | 1 | |
| V _{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 16</u> | _ | 0.82 | 1.2 | V |

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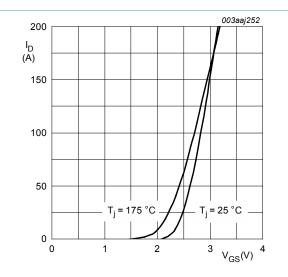
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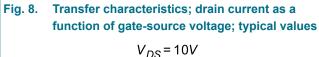
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|------|-----|------|
| t _{rr} | reverse recovery time | $I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V; | - | 30.9 | - | ns |
| Q _r | recovered charge | V _{DS} = 25 V; T _j = 25 °C | - | 36.3 | - | nC |



T_j = 25 °C; t_p = 300 μs







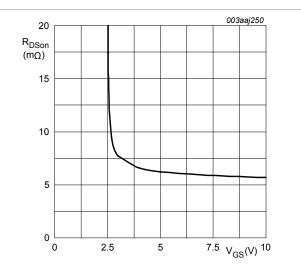


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_i = 25^{\circ}C; I_D = 25A$

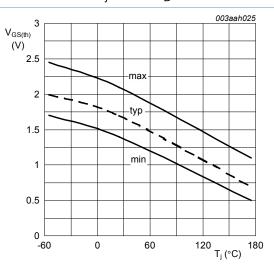


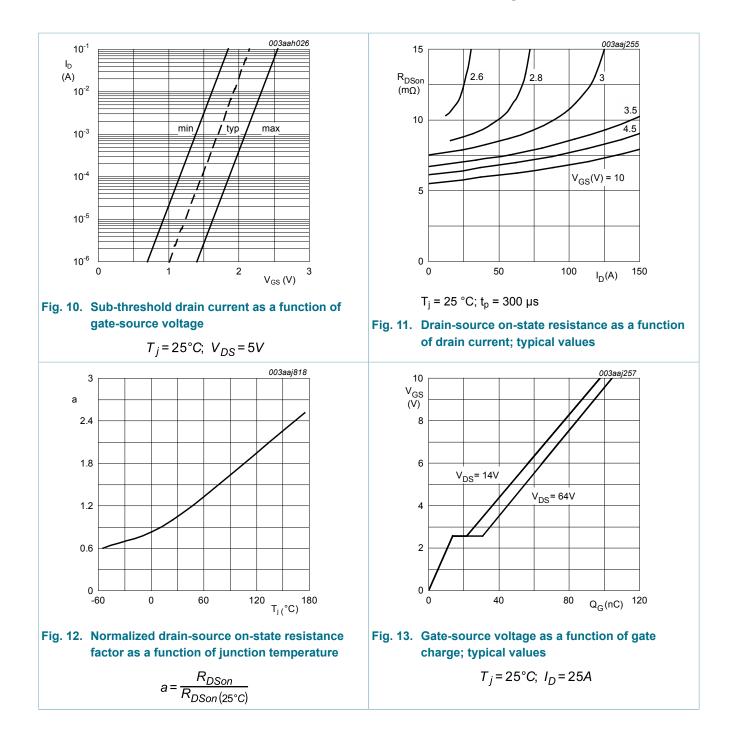
Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

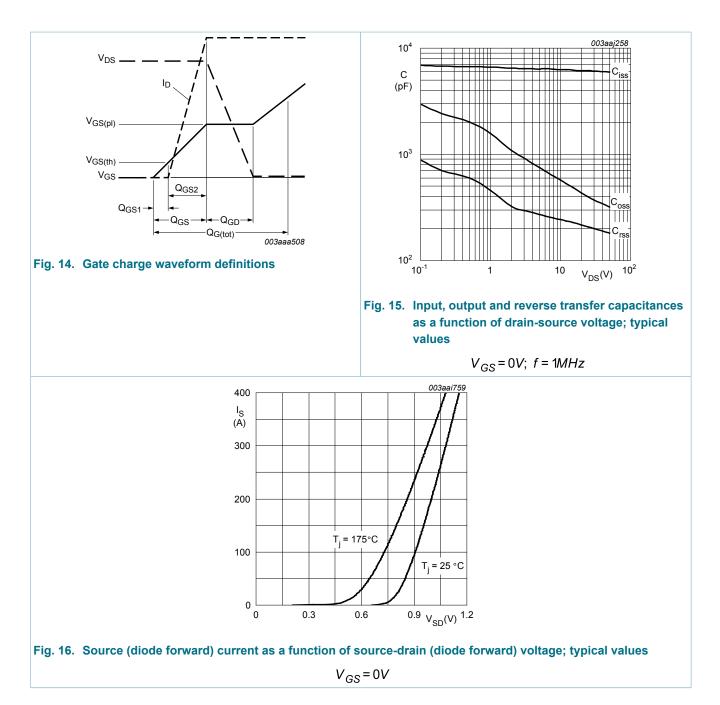
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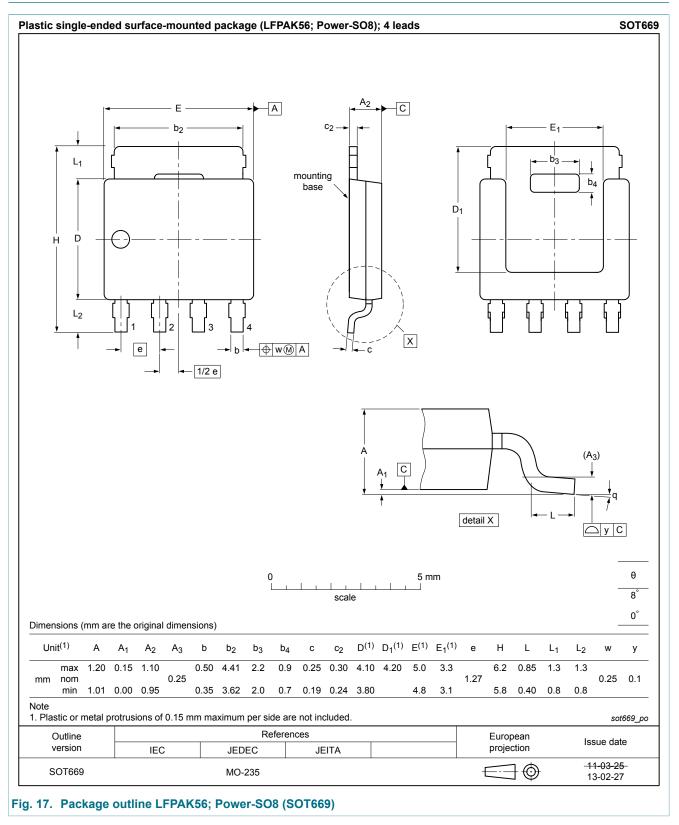


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10. Package outline



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11. Legal information

11.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
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N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56

12. Contents

| 1 | General description | 1 |
|------|-------------------------|----|
| 2 | Features and benefits | 1 |
| 3 | Applications | 1 |
| 4 | Quick reference data | 1 |
| 5 | Pinning information | 2 |
| 6 | Ordering information | 2 |
| 7 | Limiting values | 2 |
| 8 | Thermal characteristics | 4 |
| 9 | Characteristics | 5 |
| 10 | Package outline | 9 |
| 11 | Legal information | 10 |
| 11.1 | Data sheet status | |
| 11.2 | Definitions | |
| 11.3 | Disclaimers | |
| 11.4 | Trademarks | 11 |

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